



Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
60V	0.9Ω@10V	340mA
	1.1Ω@5V	

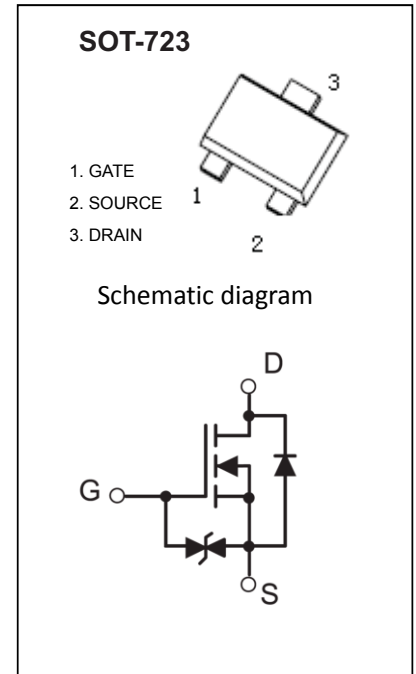
Feature

- High density cell design for Low $R_{DS(on)}$
- Voltage controlled small signal switch
- Rugged and reliable
- ESD protected Gate HBM 2.5KV

Application

- DC/DC Converter
- Load Switch for Portable Devices
- Battery Switch

MARKING:



ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	I_D	340	mA
Power Dissipation	P_D	0.225	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	556	°C/W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55~ +150	°C

MOSFET ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise noted)

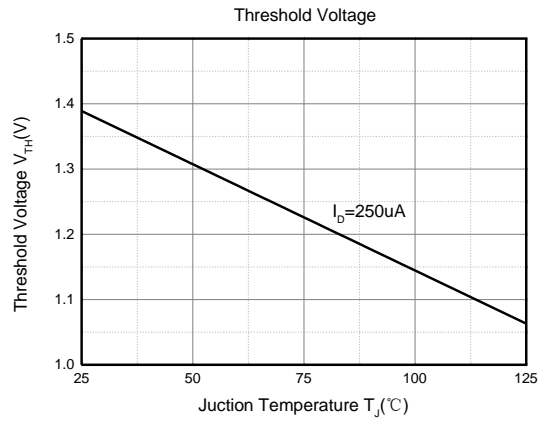
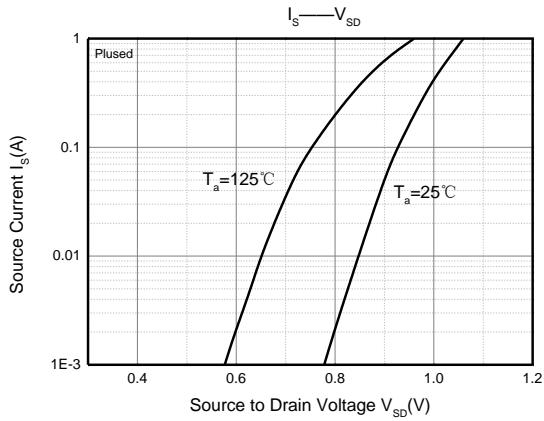
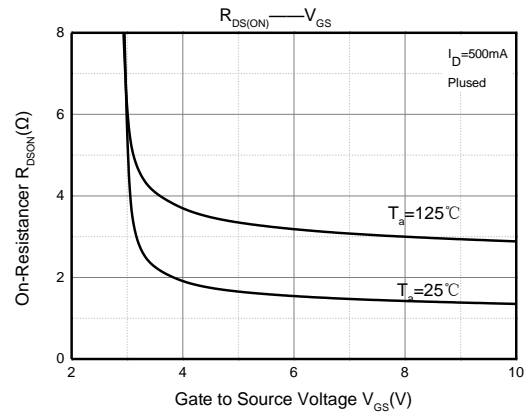
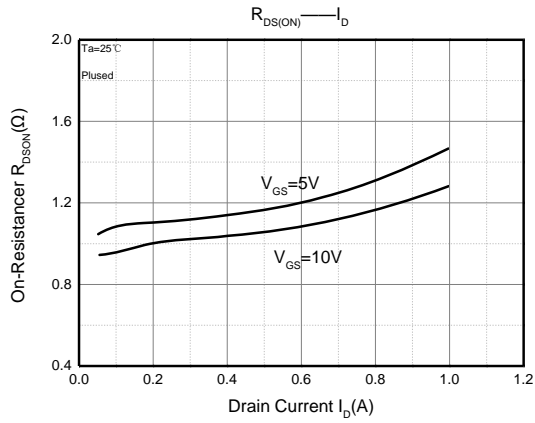
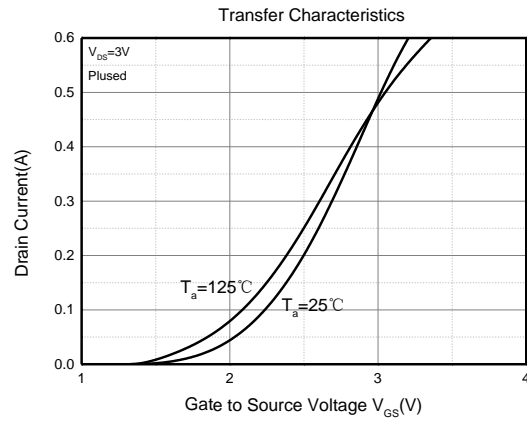
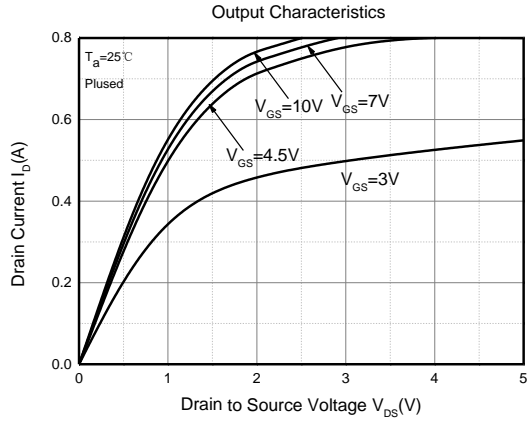
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	60			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 48V, V_{GS} = 0V$			1	μA
Gate-body leakage current	I_{GSS1}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 10	μA
	I_{GSS2}	$V_{GS} = \pm 10V, V_{DS} = 0V$			± 200	nA
	I_{GSS2}	$V_{GS} = \pm 5V, V_{DS} = 0V$			± 100	nA
Gate threshold voltage*	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1	1.6	2.5	V
Drain-source on-resistance*	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 500mA$		0.9	2.5	Ω
		$V_{GS} = 4.5V, I_D = 200mA$		1.1	3	
Recovered charge	Q_r	$V_{GS}=0V, I_S=300mA, V_R=25V,$ $di_s/dt=-100A/\mu S$		30		nC
Dynamic characteristics**						
Input Capacitance	C_{iss}	$V_{DS}=10V, V_{GS}=0V, f=1MHz$			40	pF
Output Capacitance	C_{oss}				30	
Reverse Transfer Capacitance	C_{rss}				10	
Switching Characteristics**						
Turn-on delay time	$t_{d(on)}$	$V_{GS}=10V, V_{DD}=50V, R_G=50\Omega$			10	ns
Turn-off delay time	$t_{d(off)}$	$R_{GS}=50\Omega, R_L=250\Omega$			15	
Reverse recovery Time	t_{rr}	$V_{GS}=0V, I_S=300mA, V_R=25V,$ $di_s/dt=-100A/\mu S$		30		
Source-Drain Diode characteristics						
Diode Forward voltage	V_{SD}	$V_{GS} = 0V, I_S = 300mA$		0.97	1.5	V
GATE-SOURCE ZENER DIODE						
Gate-Source Breakdown Voltage	BV_{GSO}	$I_{GS} = \pm 1mA$ (Open Drain)	± 21.5		± 30	V

Notes:

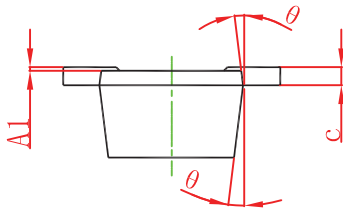
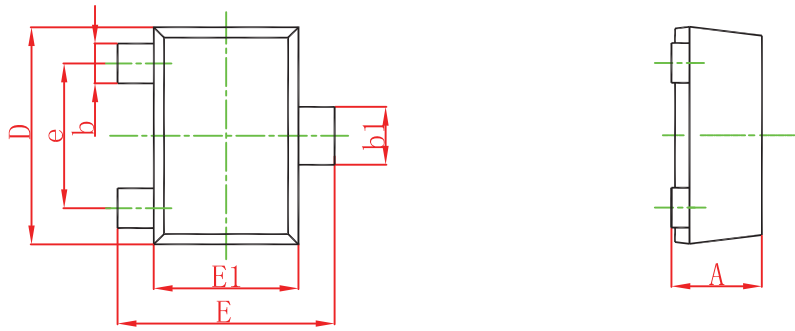
*Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.

**These parameters have no way to verify.

Typical Characteristics



SOT-723 Package Information

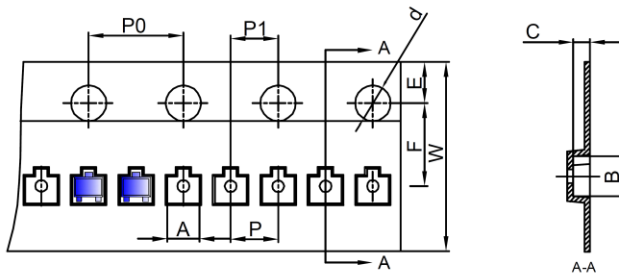


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.430	0.500	0.017	0.020
A1	0.000	0.050	0.000	0.002
b	0.170	0.270	0.007	0.011
b1	0.270	0.370	0.011	0.015
c	0.080	0.150	0.003	0.006
D	1.150	1.250	0.045	0.049
E	1.150	1.250	0.045	0.049
E1	0.750	0.850	0.030	0.033
e	0.800TYP.		0.031TYP.	
θ	7° REF.		7° REF.	

SOT-723 Tape and Reel

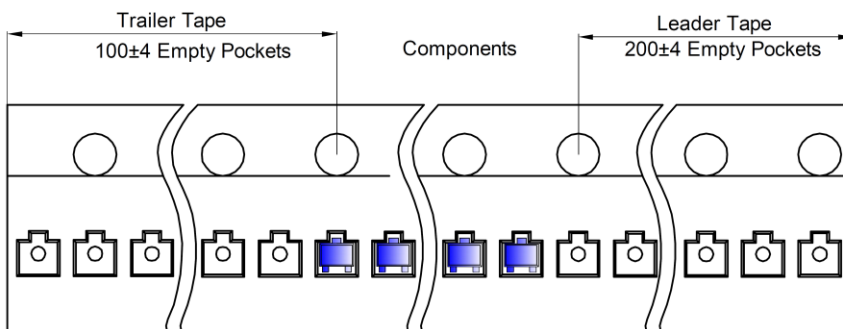
SOT-723 Tape and reel

SOT-723 Embossed Carrier Tape

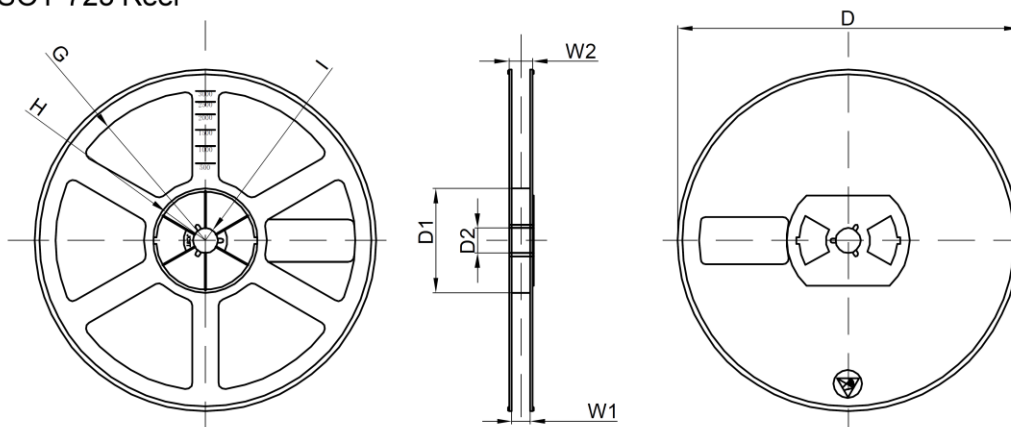


Dimensions are in millimeter											
Pkg type	A	B	C	d	E	F	P0	P	P1	W	
SOT-723	1.33	1.45	0.61	∅1.50	1.75	3.50	4.00	2.00	2.00	8.00	

SOT-723 Tape Leader and Trailer



SOT-723 Reel



Dimensions are in millimeter									
Reel Option	D	D1	D2	G	H	I	W1	W2	
7" Dia	∅178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30	

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
8000 pcs	7 inch	80,000 pcs	203×203×195	320,000 pcs	438×438×220	

单击下面可查看定价，库存，交付和生命周期等信息

[>>GP\(格瑞宝\)](#)